

Notice of References CitedApplication No.
09/405,945Applicant(s)
Bo Jin et al.Examiner
Lynette T. Umez-EroniniGroup Art Unit
1765

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	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
A	5,037,781	8/1991	Woodruff et al.	438	400
B	5,468,342	11/1995	Nulty et al.	438	714
C	5,503,901	4/1996	Sakai et al.	438	723
D	5,728,595	3/1998	Fukase	438	241
E	5,893,740	8/1991	Chang et al.	438	289
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M					

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
N	304,278 A	5/1997	Taiwan	Jang et al.	H01L	21/28
O						
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R						
S						
T						

NON-PATENT DOCUMENTS

	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
U	Jang et al., Source-drain distributed implantation method - forming gate structure and two source/drains by implanting second dopant and third area by implanting first LATI, English Abstract of TW 304278A, pp. 1 and 2.	5/1997
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